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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	09/945512
	Filing Date	August 30, 2001
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2812
	Examiner Name	Booth, Richard
Sheet 1 of 2	Attorney Docket No: 1303.027US1	

US PATENT DOCUMENTS						
Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
RB	US-2001/0013621	08/16/2001	Nakazato, K	257	314	12/08/2000
RB	US-2001/0055838	12/27/2001	Walker, A J., et al.	438	129	08/13/2001
RB	US-2002/0028541	03/07/2002	Lee, T H., et al.	438	149	08/13/2001
RB	US-5,691,209	11/25/1997	Liberkowsky, J B.	437	7	10/15/1996
RB	US-5,739,544	04/14/1998	Yuki, K., et al.	257	25	12/12/1995
RB	US-6,077,745	06/20/2000	Burns, M S., et al.	438	270	10/29/1997
RB	US-6,306,708	10/23/2001	Peng, N	438	266	02/02/2000
RB	US-6,433,382	08/13/2002	Orlowski, M., et al.	257	315	04/06/1995

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T*

OTHER DOCUMENTS - NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No*	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T*
RB		AARIK, JAAN . et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000), pp. 531-537				
RB		AARIK, JAAN . et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000), pp. 105-113				
RB		FERGUSON, J D., et al., "Atomic layer deposition of Al ₂ O ₃ and SiO ₂ on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000), pp. 280-292				
RB		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta ₂ O ₅ films", <u>Journal of the Korean Physical Society</u> , (December 2000), pp. 975-979				
RB		KIM, YEONG K., et al., "Novel capacitor technology for high density stand-alone and embedded DRAMs", <u>IEEE</u> , (2000), 4 pages				
RB		KUKLI, KAUPU , "Atomic Layer Deposition of Titanium Oxide from TiI ₄ and H ₂ O ₂ ", <u>Chemical Vapor Deposition</u> , (2000), pp. 303-310				
RB		KUKLI, KAUPU , et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001), pp. 262-272				
RB		KUKLI, KAUPU , et al., "Real-time monitoring in atomic layer deposition of TiO ₂ from TiI ₄ and H ₂ O-H ₂ O ₂ ", <u>American Chemical Society</u> , (2000), pp. 8122-8128				

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Complete if Known Application Number Filing Date First Named Inventor Group Art Unit Examiner Name	09/945512
	August 30, 2001
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LB		LEE, J., "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-AI ₂ O ₃ Gate Dielectric", <u>IEDM</u> , (2000), pp. 645-648	
LB		PARANJPE, AJIT, et al., "Atomic layer deposition of AlOx for thin film head gap application", <u>Journal of the Electrochemical Society</u> , (September 2001), pp. 465-471	
LB		SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000), 2 pages	

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